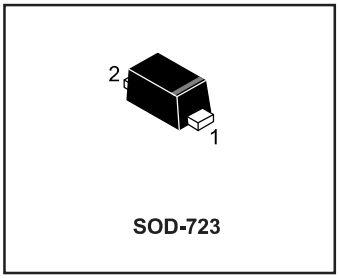
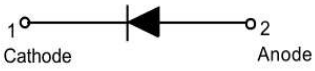
RB751G-40
S-RB751G-40

Schottky barrier diode





1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Small power mold type.
- Low VF
- High reliability.

2. Construction

- Silicon epitaxial planar

3. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
RB751G-40	5	4000/Tape&Reel

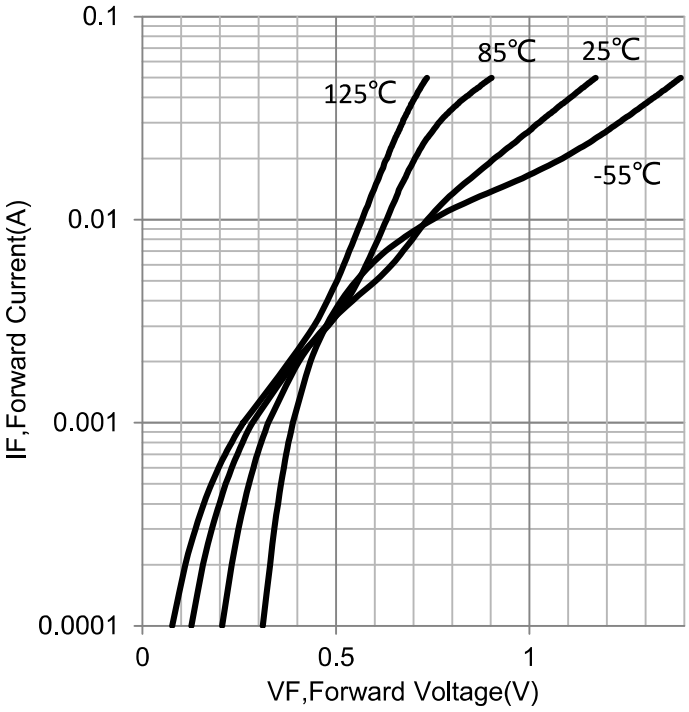
4. MAXIMUM RATINGS(Ta = 25ºC)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	VRM	40	V
Reverse voltage(DC)	VR	30	V
Average rectified forward current	IO	30	mA
Forward current surge peak (60Hz・1cyc)	IFSM	200	mA
Junction temperature	Tj	125	℃
Storage temperature	Tstg	-40~+125	℃

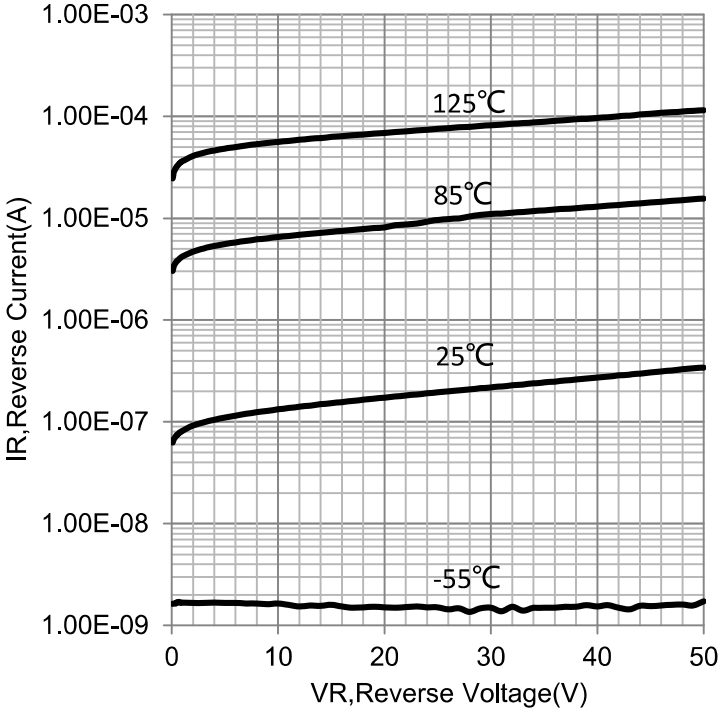
5. ELECTRICAL CHARACTERISTICS (Ta= 25ºC)

CHARACTERISTICS	Symbol	Min	Typ	Max	Unit
Forward voltage (IF=1mA)	VF	-	-	0.37	V
Reverse current (VR=30V)	IR	-	-	0.5	μA
Capacitance between terminals (VR =1V , f=1MHz)	Ct	-	0.9	-	pF

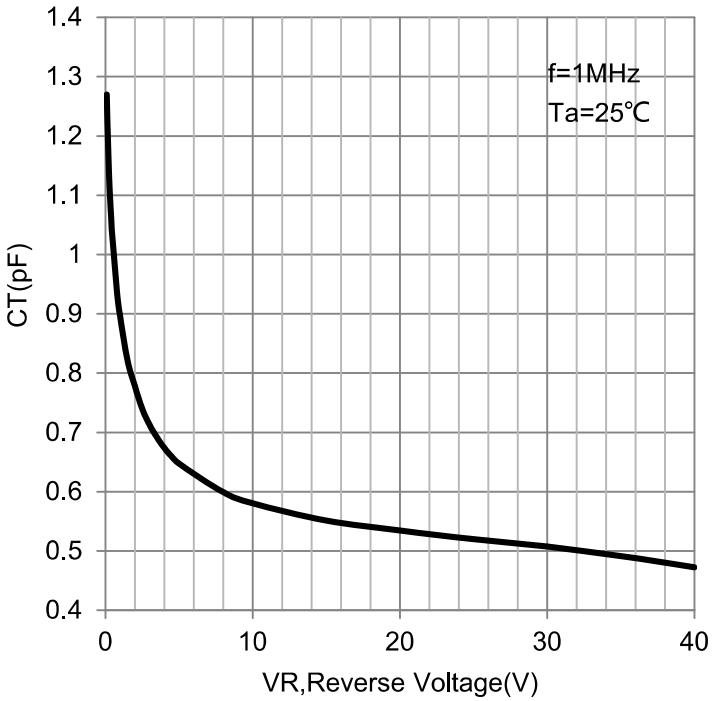
6.ELECTRICAL CHARACTERISTICS CURVES



IF vs. VF

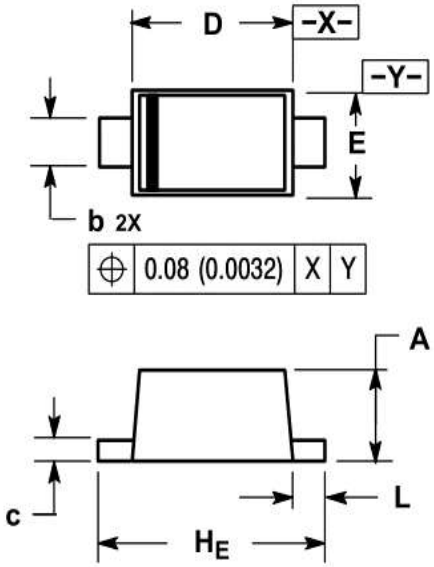


IR vs. VR



CT vs. VR

7.OUTLINE AND DIMENSIONS



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

Dim	MILLIMETERS			NCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.49	0.52	0.55	0.019	0.020	0.022
b	0.25	0.28	0.32	0.0098	0.011	0.013
c	0.08	0.12	0.15	0.0032	0.0047	0.0059
D	0.95	1.00	1.05	0.037	0.039	0.041
E	0.55	0.60	0.65	0.022	0.024	0.026
HE	1.35	1.40	1.45	0.053	0.055	0.057
L	0.15	0.2	0.25	0.006	0.0079	0.010

8.SOLDERING FOOTPRINT